TOSHIBA CCD LINEAR IMAGE SENSOR CCD(Charge Coupled Device)

# TCD132D

The TCD132D is a 1024-elements linear image sensor which includes CCD drive circuit and signal processing circuit. The CCD drive circuit consists of the pulse generator and the CCD driver; therefore it is posible to get easy drive by applying simple pulses ( $\phi_{M}$ ,  $\phi_{CCD}$  and SH).

The signal processing circuit which consists of the clamp circuit and S/H circuit and pre-amplifier.



• Number of Image Sensing Elements: 1024

• Image Sensing Element Size :  $14\mu m$  by  $14\mu m$  on  $14\mu m$ 

centers

Photo Sensing Region : Low dark current pn photodiode

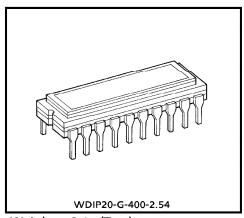
Clock : 3 Input pulses 5V

Internal Circuit : Clamp circuit (for optical black level reference)

Sample & hold circuit

Pre-amplifier

• Package : 22 pin cerdip



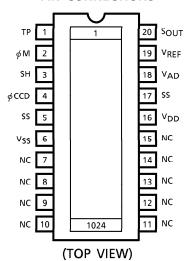
Weight: 3.1g (Typ.)

#### **MAXIMUM RATINGS** (Note 1)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Master Clock Voltage	V∮M		V
CCD Clock Voltage	V∳CCD		٧
Shift Pulse Voltage	$v_{SH}$		V
Reference Voltage	V <sub>REF</sub>	- 0.3~15	V
Power Supply Voltage (Analog)	V <sub>AD</sub>	-0.5~15	٧
Power Supply Voltage (Digital)	V <sub>DD</sub>		V
Operating Temperature	T <sub>opr</sub>	- 25~60	°C
Storage Temperature	T <sub>stg</sub>	<b>-40∼100</b>	°C

(Note 1) All voltage are with respect to SS and V<sub>SS</sub> terminals (Ground).

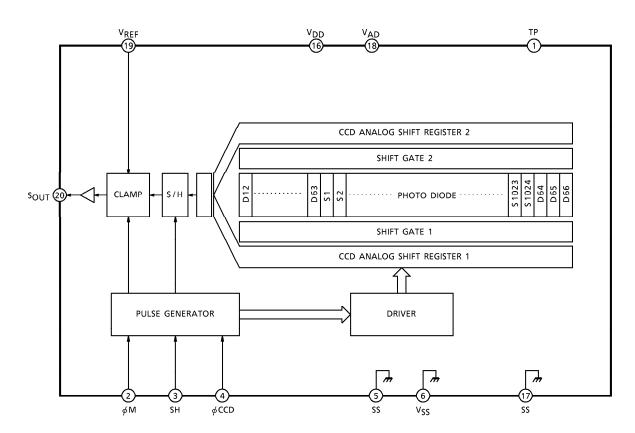
### PIN CONNECTIONS



#### 961001EBA2

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### **CIRCUIT DIAGRAM**



### **PIN NAMES**

φM	Master Clock
φccd	CCD Clock
SH	Shift Pulse
V <sub>REF</sub>	Reference Voltage Input
SOUT	Signal Output
$V_{AD}$	Power (Analog)
$V_{DD}$	Power (Digital)
SS	Ground (Analog)
V <sub>SS</sub>	Ground (Digital)
TP	Test Input
NC	Non Connection

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### **OPTICAL / ELECTRICAL CHARACTERISTICS**

(Ta = 25°C,  $V_{AD} = V_{DD} = 12V$ ,  $V_{\phi M} = V_{\phi CCD} = V_{SH} = 5V$  (PULSE),  $V_{REF} = 5.0V$ ,  $f_{\phi CCD} = 0.5$ MHz,  $t_{INT}$  (INTEGRATION TIME) = 10ms, LIGHT SOURCE = DAYLGIHT FLUORESCENT LAMP, LOAD RESISTANCE = 100k $\Omega$ )

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Sensitivity	R	9	12	15	V / lx·s	(Note 2)
Photo Response Non Uniformity	PRNU	_	_	10	%	(Note 3)
Saturation Output Voltage	V <sub>SAT</sub>	2	3	_	V	(Note 4)
Saturation Exposure	SE	0.13	0.25		lx∙s	(Note 5)
Dark Signal Non Uniformity	DSNU	_	_	15	mV	(Note 6)
Analog Current Dissipation	I <sub>AD</sub>	_	12	20	mA	
Digital Current Dissipation	I <sub>DD</sub>	_	4	10	mA	
Input Current of V <sub>REF</sub>	I <sub>REF</sub>	_	0.1	1	mA	
Total Transfer Efficiency	TTE	92	_		%	
Output Impedance	ZO	_	1	2	kΩ	
Clamp Error Voltage	V <sub>ERR</sub>		100	200	V	(Note 7)

(Note 2) Sensitivity for 2856K W-lamp is 25V/lx·s (Typ.)

(Note 3) Measured at 50% of SE (Typ.)

Definition of PRNU : PRNU =  $\frac{\Delta \chi}{\overline{\chi}}$  × 100 (%)

Where  $\overline{\chi}$  is average of total signal outputs and  $\Delta \chi$  is the maximum deviation from  $\overline{\chi}$  under uniform illumination.

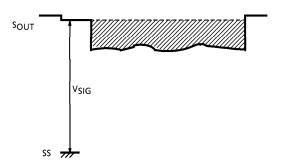
(Note 4) V<sub>SAT</sub> is defined as minimum saturation output voltage of all effective pixels.

(Note 5) Definition of SE : SE =  $\frac{V_{SAT}}{R}$  (Ix·s)

(Note 6) Definition of DSNU: DSNU = MAX - MIN (mV)



(Note 7) Definition of  $V_{ERR}$ :  $V_{ERR} = |V_{REF} - V_{SIG}|$  Where  $V_{SIG}$  is defined below.



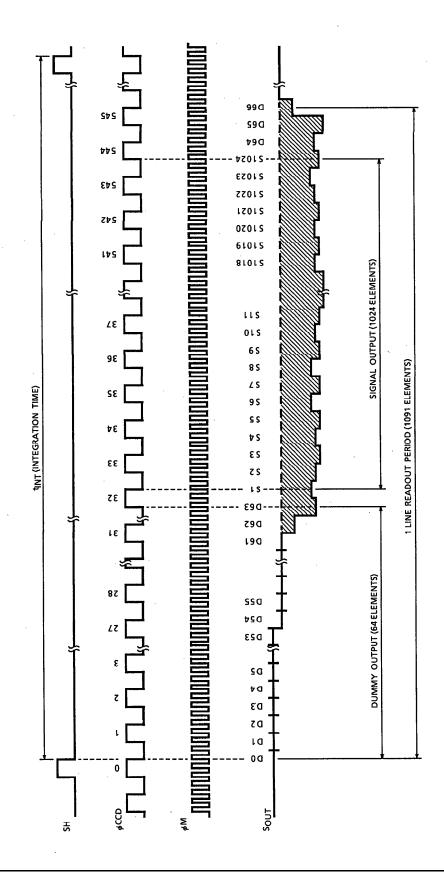
# **OPERATING CONDITION**

CHARACTERISTIC		SYMBOL	MIN.	TYP.	MAX.	UNIT
Master Clock Voltage	"H" Level	V <sub>∳</sub> M	4.5	5.0	5.5	V
	"L" Level		0	0.5	0.8	
ICCD Clack Valtage	"H" Level	$V_{\phi}CCD$	4.5	5.0	5.5	V
	"L" Level		0	0.5	0.8	
Shift Dulsa Valtaga	"H"Level	Vari	4.5	5.0	5.5	٧
Shift Pulse Voltage	"L" Level	$V_{SH}$	0	0.5	0.8	V
Reference Voltage		$V_{REF}$	4.5	5.0	5.5	V
Power Supply Voltage (Analog)		$V_{AD}$	11	12	13	V
Power Supply Voltage ((Driver)		$V_{DD}$	11	12	13	V
Test Input Voltage		V <sub>TP</sub>	0	0	0.8	٧

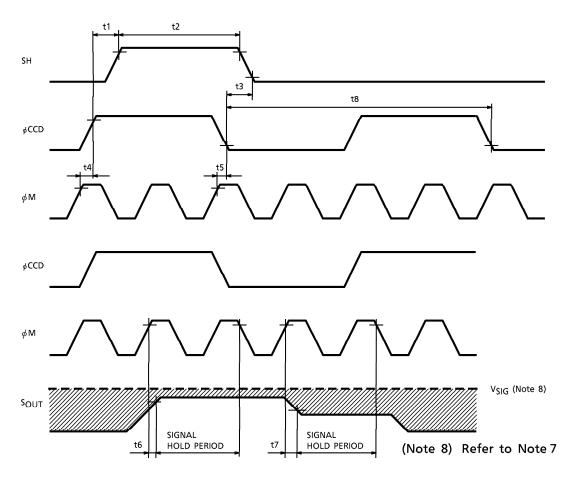
# **CLOCK CHARACTERISTICS** (Ta = 25°C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Master Clock Frequency	f <sub>øM</sub>	0.4	2	4	MHz
Data Rate	fDATA	0.2	1	2	MHz
CCD Clock Frequency	$f_{\phi}CCD$	0.1	0.5	1.0	MHz
Master Clock Capacitance	C <sub>øM</sub>	_	_	10	pF
CCD Clock Capacitance	$C_{\phi}CCD$	_	_	10	pF
Shift Pulse Capacitance	C <sub>SH</sub>	_	-	10	pF

TIMING CHART

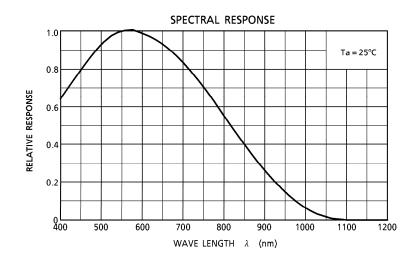


# TIMING REQUIREMENTS

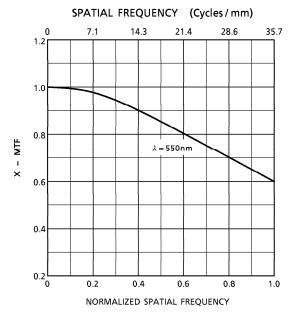


CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Pulse Timing of SH and $\phi_{CCD}$	t1, t3	0	20	60	ns
SH Pulse Width	t2	250	_	t8/2	ns
Pulse Timing of $\phi_{M}$ and $\phi_{CCD}$	t4, t5	0	20	60	ns
Aperture Delay	t6, t7	_	80	120	ns
$\phi_{CCD}$ Period	t8	1	2	10	$\mu$ s

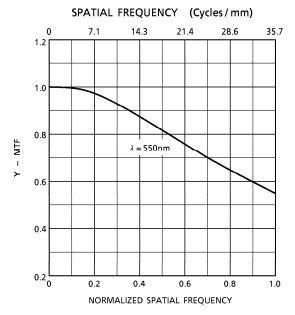
## **TYPICAL PERFORMANCE CURVES**



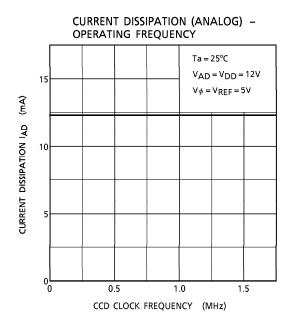
MODULATION TRANSFER FUNCTION OF X-DIRECTION

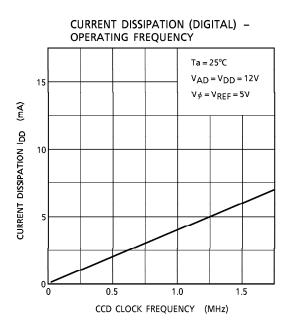


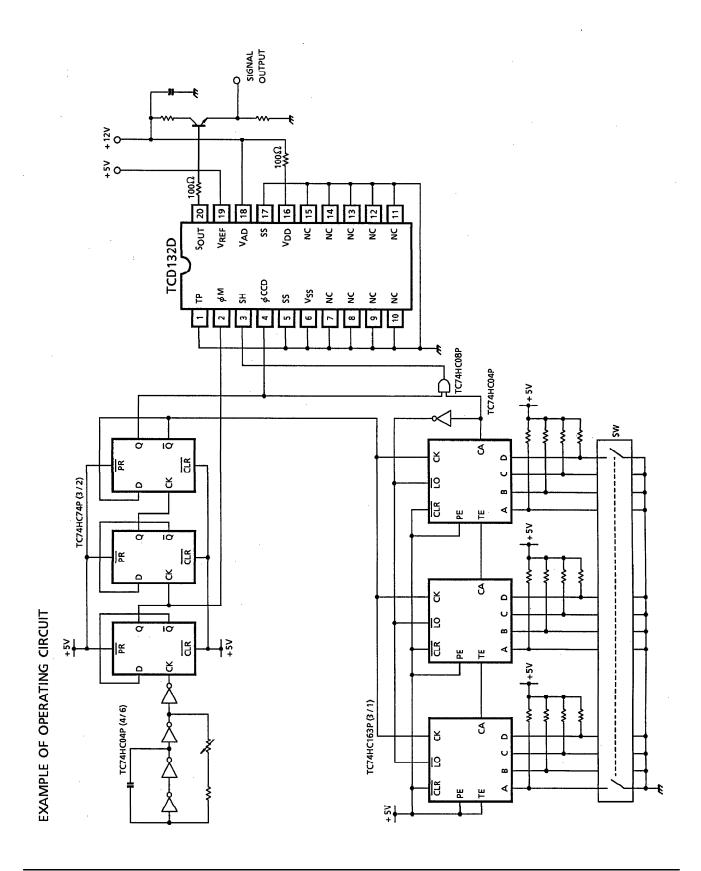
MODULATION TRANSFER FUNCTION OF Y-DIRECTION



# TYPICAL PERFORMANCE CURVES (Cont'd)







#### **CAUTION**

# 1. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor.

Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N<sub>2</sub>.

Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

### 2. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

## 3. Incident Light

CCD sensor is sensitive to infrared light.

Note that infrared light component degrades resolution and PRNU of CCD sensor.

### 4. Lead Frame Forming

Since this package is not stout against mechanical stress, you should not reform the lead frame. We recommend to use a IC-inserter when you assemble to PCB.

# **OUTLINE DRAWING**

WDIP20-G-400 (B)

7.1±0.8 (Note 1) 14.3(14 \( \mu \times 1024 \)

20

11

26.0±0.5

26.0±0.5

1.57TYP

1.57TYP

1.57TYP

1.31±0.1

(Note 1) No. 1 SENSOR ELEMENT (S1) TO EDGE OF PACKAGE.

(Note 2) TOP OF CHIP TO BOTTOM OF PACKAGE.

(Note 3) GLASS THICKNES (n = 1.5)

Weight: 3.1g (Typ.)